

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	(semiconductor and power and substrate and voltage and sustain\$3 and trench and column and diffus\$3 and sidewall and adjacent and vertical\$3 and fill\$3 and junction). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 16:58
L2	6	(semiconductor and power and substrate and voltage and sustain\$3 and trench and barrier and etch\$3 and fill\$3 and diffus\$3 and overlap\$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 17:00